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Deformation Methods for Investigation of the Deep Level Parameters in Semiconductors

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**Abstract:** In this paper deformation methods are offered to investigate deep level parameters in semiconductors. It is based on strain parameters measurements of compensated and overcompensated semiconductors. The dynamic changes of current flow in compensated and overcompensated samples of p-type Si: Ni and n-type Si: Mn under uniform pulse hydrostatic compression (UHC) was investigated. It was observed that in p-type Si: Ni samples ionization energy levels Ni at UHC increases, on the contrary in samples n-type Si: Mn it decreases. The ionization energy and baric coefficient of the shift of Ni and Mn levels were bounded.

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